

## SWITCHMODE SERIES NPN POWER TRANSISTORS

... designed for use in high-voltage, high-speed, power switching applications such as switching regulator's, inverters, and converter.

### FEATURES:

\*Collector-Emitter Sustaining Voltage-

$$V_{CEO(sus)} = 800 \text{ V (Min)}$$

\* Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 2.0 \text{ V (Max.) @ } I_C = 1.5 \text{ A, } I_B = 0.3 \text{ A}$$

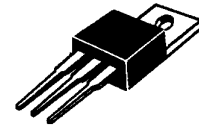
\* Switching Time -  $t_f = 0.7 \text{ us (Max.) @ } I_C = 2.0 \text{ A}$

**NPN**  
**2SC3150**

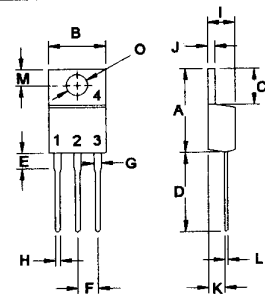
**3 AMPERE**  
**SILICON POWER**  
**TRANSISTORS**  
**800 VOLTS**  
**50 WATTS**

### MAXIMUM RATINGS

Characteristic	Symbol	2SC3150	Unit
Collector-Emitter Voltage	$V_{CEO}$	800	V
Collector-Base Voltage	$V_{CBO}$	900	V
Emitter-Base Voltage	$V_{EBO}$	7.0	V
Collector Current - Continuous - Peak	$I_C$ $I_{CM}$	3.0 10	A
Base current	$I_B$	1.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	50 0.4	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$



**TO-220**

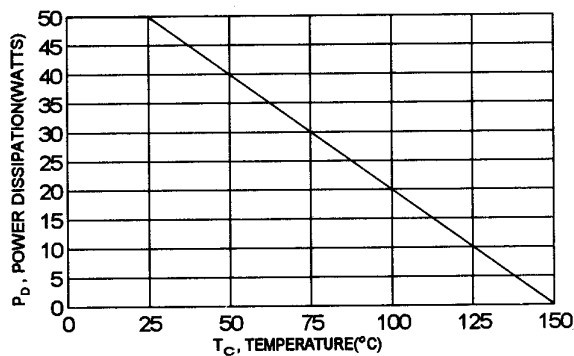


PIN 1.BASE  
2.COLLECTOR  
3.EMITTER  
4.COLLECTOR(CASE)

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	2.5	$^\circ\text{C/W}$

FIGURE -1 POWER DERATING



DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

**ELECTRICAL CHARACTERISTICS** (  $T_c = 25^\circ\text{C}$  unless otherwise noted )

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Sustaining Voltage ( $I_C = 3.0\text{ A}$ , $I_B = 1.0\text{ A}$ , $L = 500\text{ }\mu\text{H}$ )	$V_{CEO(SUS)}$	800		V
Collector-Emitter Breakdown Voltage ( $I_C = 5.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	800		V
Collector-Base Breakdown Voltage ( $I_C = 1.0\text{ mA}$ , $I_E = 0$ )	$V_{(BR)CBO}$	900		V
Emitter-Base Breakdown Voltage ( $I_C = 1.0\text{ mA}$ , $I_C = 0$ )	$V_{(BR)EBO}$	7.0		V
Collector Cutoff Current ( $V_{CB} = 800\text{ V}$ , $I_E = 0$ )	$I_{CBO}$		10	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = 5.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$		10	$\mu\text{A}$

**ON CHARACTERISTICS (1)**

DC Current Gain ( $I_C = 0.2\text{ A}$ , $V_{CE} = 5.0\text{ V}$ ) * ( $I_C = 1.0\text{ A}$ , $V_{CE} = 5.0\text{ V}$ )	$h_{FE(2)}$ $h_{FE}$	10 8.0	40	
Collector-Emitter Saturation Voltage ( $I_C = 1.5\text{ A}$ , $I_B = 300\text{ mA}$ )	$V_{CE(sat)}$		2.0	V
Base-Emitter Saturation Voltage ( $I_C = 1.5\text{ A}$ , $I_B = 300\text{ mA}$ )	$V_{BE(sat)}$		1.5	V

**DYNAMIC CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C = 0.2\text{ A}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$f_T$	7.0		MHz
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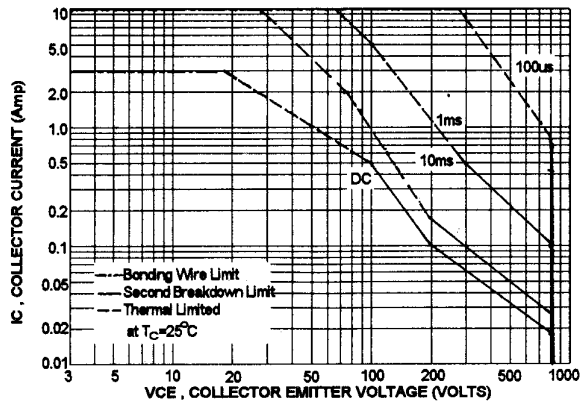
**SWITCHING CHARACTERISTICS**

On Time	$V_{CC} = 400\text{ V}$ , $I_C = 2.0\text{ A}$ $I_{B1} = 0.4\text{ A}$ , $I_{B2} = -0.8\text{ A}$ $R_L = 200\text{ }\Omega$	$t_{on}$	1.0	$\mu\text{s}$
Storage Time		$t_s$	3.0	$\mu\text{s}$
Fall Time		$t_f$	0.7	$\mu\text{s}$

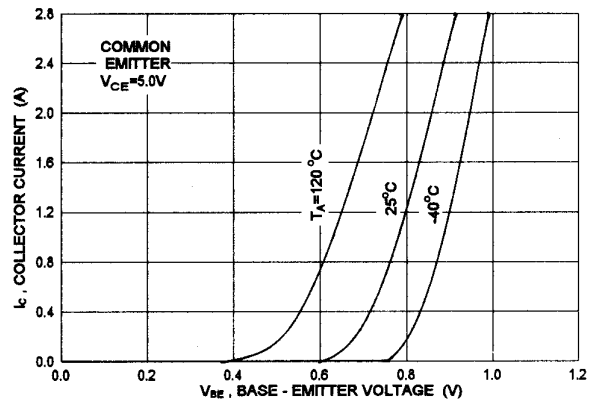
(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ \*  $h_{FE(2)}$  Classification:

10	K	20	15	L	30	20	M	40
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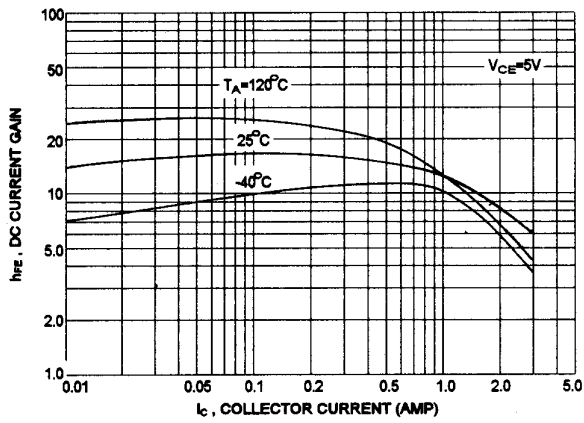
SAFE OPERATING AREA



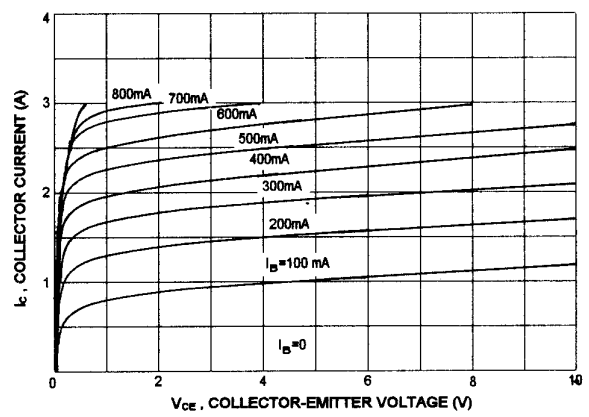
IC - Vbe



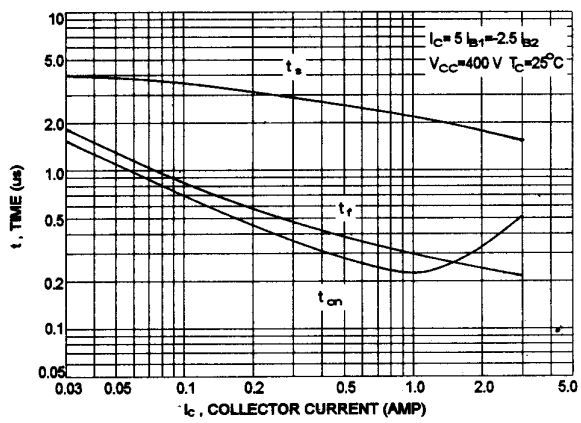
DC CURRENT GAIN



IC - Vce



SWITCHING TIME



"ON" VOLTAGES

